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IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Narihiro MOROSAWA et al. Conf.: 7107
Appl. No.: 09/471,173 Group: 2826
Filed: December 23, 1999 Examiner: K. Quinto
For: INSULATED GATE TRANSISTOR AND PROCESS FOR
FABRICATING THE SAME

RECEIVED
AUG 13 2002
TECHNOLOGY CENTER 2800

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

August 9, 2002

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amend the claims as follows:

C¹
2. (Three Times Amended) An insulated gate transistor having a gate electrode on a substrate with a gate insulator interposed therebetween, wherein the gate insulator including silicon and oxygen contains both nitrogen atoms and fluorine atoms, and wherein nitrogen atom concentration of the gate insulator is more than $1 \times 10^{20} \text{ cm}^{-3}$, and flat band voltage is stable even if fluorine injection occurs.